

**Amendments to the Claims:**

This listing of claims will replace the listing of claims as pending in the present application:

**Listing of Claims:**

Claim 1 (original): High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, and an oxygen content of 40wtppm or less.

Claim 2 (original): High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.

Claim 3 (original): High purity hafnium and a target and thin film formed from said high purity hafnium according to claim 1 having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.

Claim 4 (canceled).

Claim 5 (original): A manufacturing method of high purity hafnium wherein a hafnium sponge raw material is subject to solvent extraction and thereafter dissolved, and the obtained hafnium ingot is further subject to deoxidation with molten salt.

Claim 6 (original): A manufacturing method of high purity hafnium according to claim 5 wherein, after performing deoxidation with molten salt, electron beam melting is further performed.